

INT-A-PAK "Half-Bridge" (Ultrafast Speed IGBT), 209 A



INT-A-PAK

FEATURES

- Generation 5 Non Punch Through (NPT) technology
- Ultrafast: Optimized for hard switching speed 8 kHz to 60 kHz
- Low $V_{CE(on)}$
- 10 μ s short circuit capability
- Square RBSOA
- Positive $V_{CE(on)}$ temperature coefficient
- HEXFRED[®] antiparallel diode with ultrasoft reverse recovery characteristics
- Industry standard package
- Al_2O_3 DBC
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed for industrial level


RoHS
COMPLIANT

PRODUCT SUMMARY

V_{CES}	600 V
I_C DC	209 A
$V_{CE(on)}$ at 200 A, 25 °C	2.6 V

BENEFITS

- Benchmark efficiency for UPS and welding application
- Rugged transient performance
- Direct mounting on heatsink
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25\text{ °C}$	209	A
		$T_C = 80\text{ °C}$	142	
Pulsed collector current	I_{CM}		400	
Clamped inductive load current	I_{LM}		400	
Diode continuous forward current	I_F	$T_C = 25\text{ °C}$	178	
		$T_C = 80\text{ °C}$	121	
Gate to emitter voltage	V_{GE}		± 20	V
Maximum power dissipation	P_D	$T_C = 25\text{ °C}$	781	W
		$T_C = 80\text{ °C}$	438	
Isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ minute	2500	V



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{BR(CES)}	V _{GE} = 0 V, I _C = 500 μA	600	-	-	V
Collector to emitter voltage	V _{CE(on)}	V _{GE} = 15 V, I _C = 100 A	-	1.95	2.1	
		V _{GE} = 15 V, I _C = 200 A	-	2.6	2.84	
		V _{GE} = 15 V, I _C = 100 A, T _J = 125 °C	-	2.28	2.5	
		V _{GE} = 15 V, I _C = 200 A, T _J = 125 °C	-	3.14	3.48	
Gate threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 500 μA	3	4.2	6	
Collector to emitter leakage current	I _{CES}	V _{GE} = 0 V, V _{CE} = 600 V	-	0.005	0.2	mA
		V _{GE} = 0 V, V _{CE} = 600 V, T _J = 150 °C	-	0.01	15	
Diode forward voltage drop	V _{FM}	I _C = 100 A	-	1.39	1.78	V
		I _C = 200 A	-	1.64	2.2	
		I _C = 100 A, T _J = 125 °C	-	1.32	1.69	
		I _C = 200 A, T _J = 125 °C	-	1.67	2.30	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V	-	-	± 200	nA

SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on switching loss	E _{on}	I _C = 200 A, V _{CC} = 360 V, V _{GE} = 15 V, R _g = 10 Ω, L = 200 μH, T _J = 25 °C	-	3.65	-	mJ
Turn-off switching loss	E _{off}		-	6.9	-	
Total switching loss	E _{tot}		-	10.55	-	
Turn-on switching loss	E _{on}	I _C = 200 A, V _{CC} = 360 V, V _{GE} = 15 V, R _g = 10 Ω, L = 200 μH, T _J = 125 °C	-	3.8	-	ns
Turn-off switching loss	E _{off}		-	7.8	-	
Total switching loss	E _{tot}		-	11.6	-	
Turn-on delay time	t _{d(on)}		-	507	-	
Rise time	t _r		-	133	-	
Turn-off delay time	t _{d(off)}		-	538	-	
Fall time	t _f	-	92	-		
Reverse bias safe operating area	RBSOA	T _J = 150 °C, I _C = 400 A, R _g = 27 Ω, V _{GE} = 15 V to 0	Fullsquare			
Short circuit safe operating area	SCSOA	T _J = 150 °C, V _{CC} = 400 V, V _P = 600 V, R _g = 27 Ω, V _{GE} = 15 V to 0	10	-	-	
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _{CC} = 400 V, T _J = 25 °C	-	226	260	ns
Diode peak reverse current	I _{rr}		-	17	20	A
Diode recovery charge	Q _{rr}		-	1900	2600	nC
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _{CC} = 400 V, T _J = 125 °C	-	290	330	ns
Diode peak reverse current	I _{rr}		-	25	30	A
Diode recovery charge	Q _{rr}		-	3600	5000	nC

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Operating junction and storage temperature range	T_J, T_{Stg}	- 40	-	150	°C
Junction to case per leg	IGBT	-	0.13	0.16	°C/W
	Diode	-	0.19	0.32	
Case to sink per module	R_{thCS}	-	0.1	-	
Mounting torque	case to heatsink	-	-	4	Nm
	case to terminal 1, 2, 3	-	-	3	
Weight		-	185	-	g

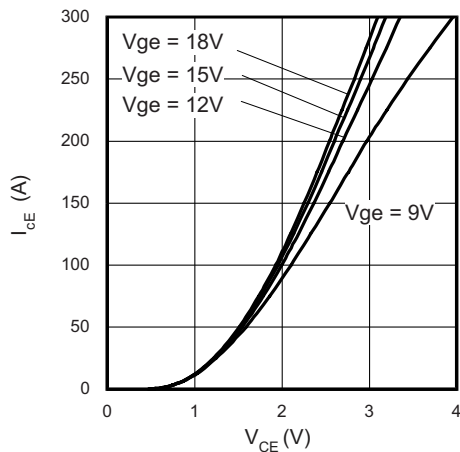


Fig. 1 - Typical IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$, $t_p = 500 \mu\text{s}$

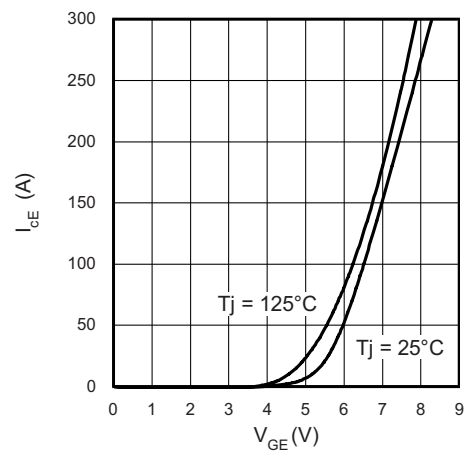


Fig. 3 - Typical Transfer Characteristics
 $V_{CE} = 20 \text{ V}$, $t_p = 500 \mu\text{s}$

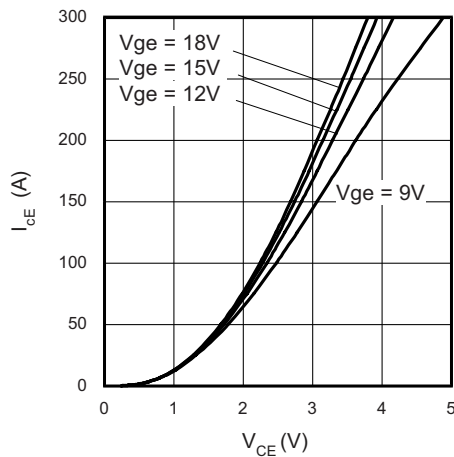


Fig. 2 - Typical IGBT Output Characteristics
 $T_J = 125^\circ\text{C}$, $t_p = 500 \mu\text{s}$

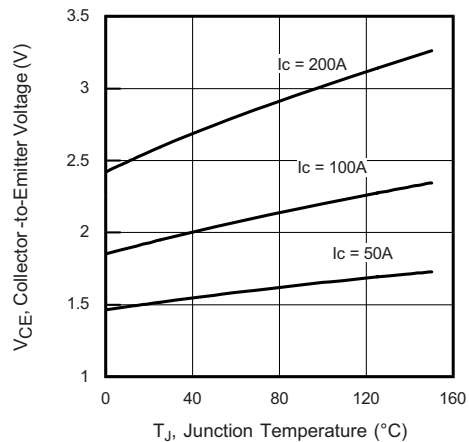


Fig. 4 - Typical Collector to Emitter Voltage vs. Junction Temperature

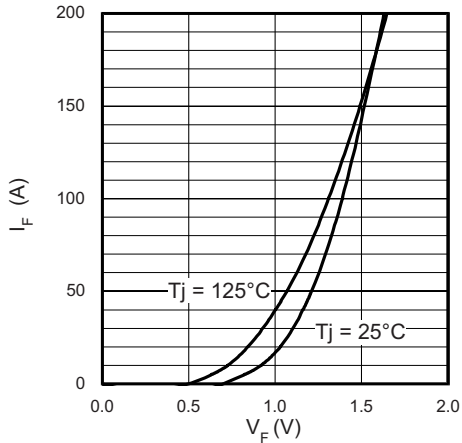


Fig. 5 - Diode Forward Characteristics,
 $t_p = 500 \mu s$

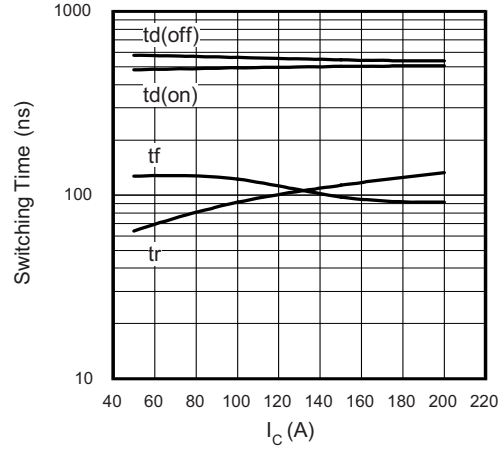


Fig. 8 - Typical Switching Time vs. I_C
 $T_J = 125^\circ C$, $L = 200 \mu H$, $V_{CC} = 360 V$,
 $R_g = 10 \Omega$, $V_{GE} = 15 V$

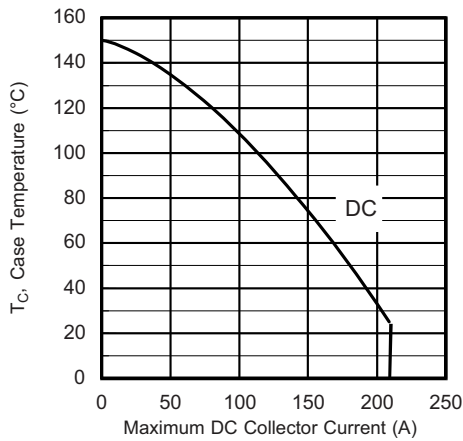


Fig. 6 - Maximum Collector Current vs.
Case Temperature

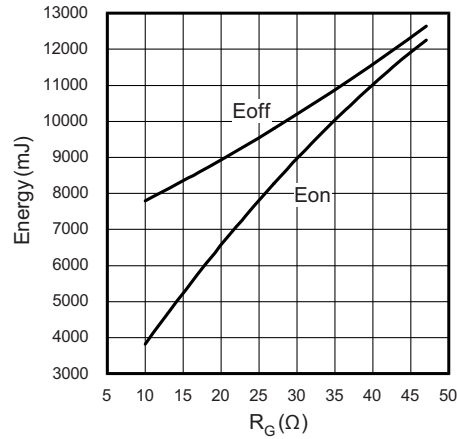


Fig. 9 - Typical Energy Loss vs. R_g
 $T_J = 125^\circ C$, $L = 200 \mu H$, $V_{CC} = 360 V$,
 $I_{CE} = 200 A$, $V_{GE} = 15 V$

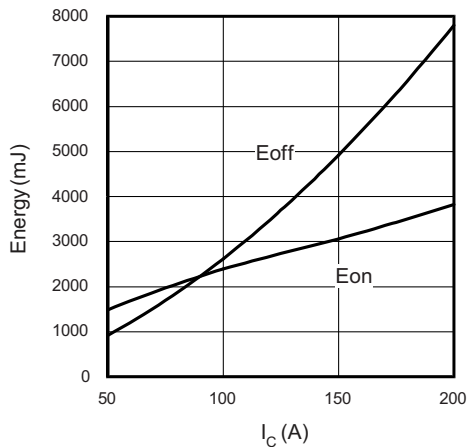


Fig. 7 - Typical Energy Loss vs. I_C
 $T_J = 125^\circ C$, $L = 200 \mu H$, $V_{CC} = 360 V$,
 $R_g = 10 \Omega$, $V_{GE} = 15 V$

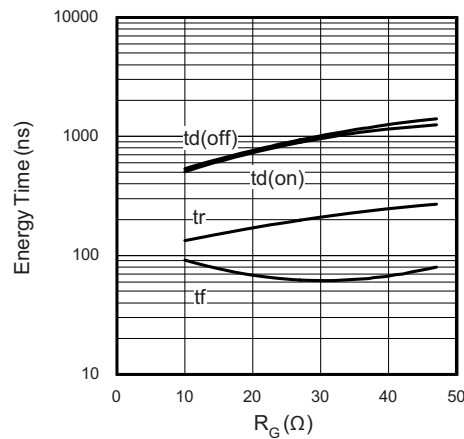


Fig. 10 - Typical Switching Time vs. R_g
 $T_J = 125^\circ C$, $L = 200 \mu H$, $V_{CC} = 360 V$,
 $I_{CE} = 200 A$, $V_{GE} = 15 V$

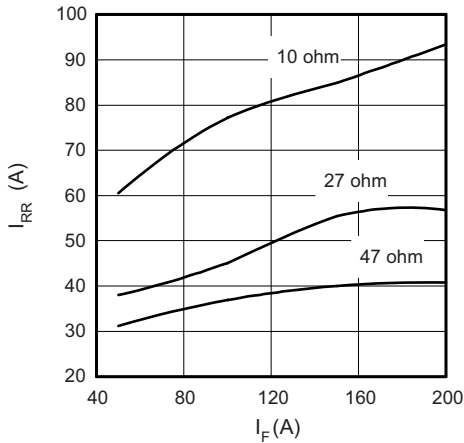


Fig. 11 - Typical Diode I_{rr} vs. I_F
 $T_J = 125^\circ\text{C}$

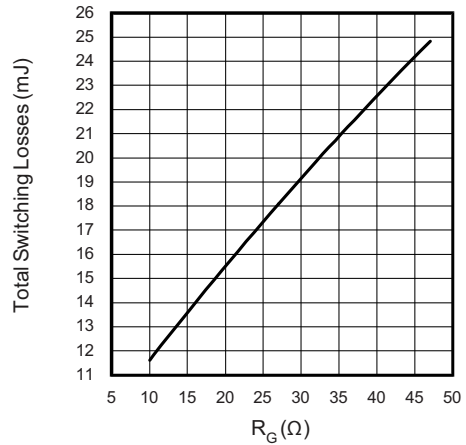


Fig. 14 - Typical Switching Losses vs. Gate Resistance
 $T_J = 125^\circ\text{C}$, $L = 200 \mu\text{H}$, $R_G = 10 \Omega$,
 $V_{CC} = 360 \text{ V}$, $V_{GE} = 15 \text{ V}$

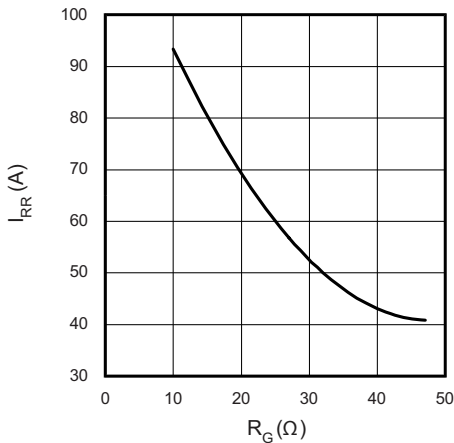


Fig. 12 - Typical Diode I_{rr} vs. R_g
 $T_J = 125^\circ\text{C}$, $I_F = 200 \text{ A}$

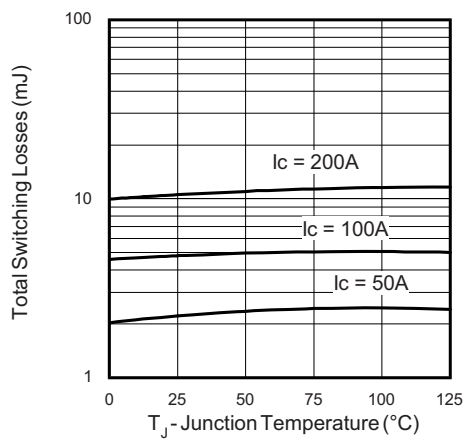


Fig. 15 - Typical Switching Losses vs. Junction Temperature;
 $L = 200 \mu\text{H}$, $R_g = 10 \Omega$, $V_{CC} = 360 \text{ V}$, $V_{GE} = 15 \text{ V}$

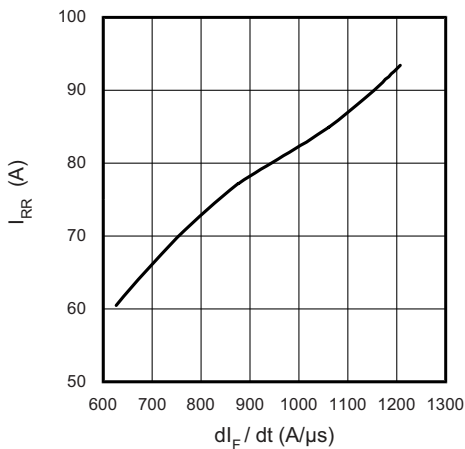


Fig. 13 - Typical Diode I_{rr} vs. di_F/dt
 $T_J = 125^\circ\text{C}$, $V_{CC} = 360 \text{ V}$, $I_F = 200 \text{ A}$, $V_{GE} = 15 \text{ V}$

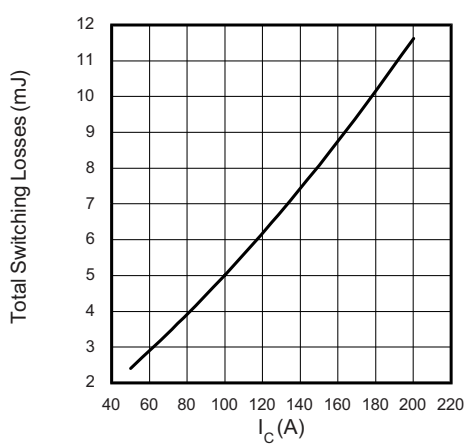


Fig. 16 - Typical Switching Losses vs. Collector to Emitter Current;
 $T_J = 125^\circ\text{C}$, $R_{g1} = 10 \Omega$, $R_{g2} = 0 \Omega$, $V_{CC} = 360 \text{ V}$, $V_{GE} = 15 \text{ V}$

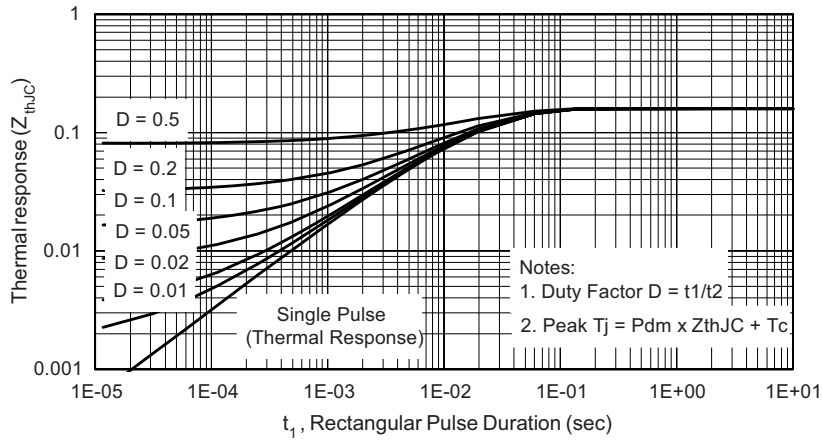


Fig. 17 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

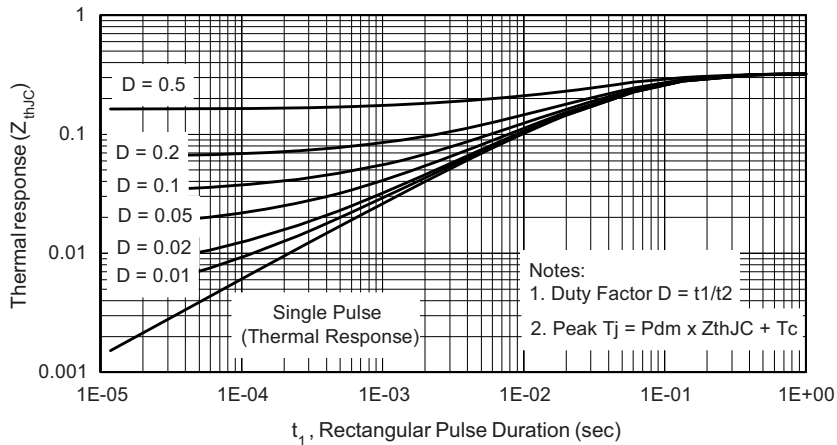


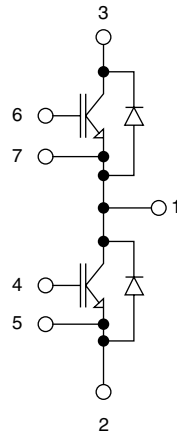
Fig. 18 - Maximum Transient Thermal Impedance, Junction to Case (HEXFRED®)

ORDERING INFORMATION TABLE

Device code	G	B	200	T	S	60	N	PbF
	①	②	③	④	⑤	⑥	⑦	⑧

- 1** - Insulated Gate Bipolar Transistor (IGBT)
- 2** - B = IGBT Generation 5 NPT
- 3** - Current rating (200 = 200 A)
- 4** - Circuit configuration (T = Half-bridge)
- 5** - Package indicator (S = INT-A-PAK)
- 6** - Voltage rating (60 = 600 V)
- 7** - Speed/type (N = Ultrafast IGBT)
- 8** - Lead (Pb)-free

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95173

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All product specifications and data are subject to change without notice.

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